

General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

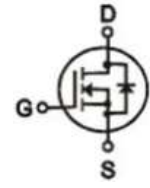
Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- SMPS 2nd Synchronous Rectifier
- BLDC Motor driver

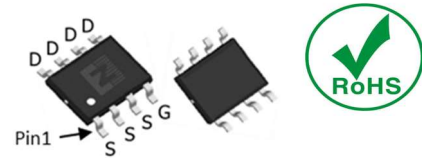
Product Summary



$V_{DS} = -60V$

$R_{DS(ON)} = 93m\Omega$

$I_D = -3.5A$



SOP-8

Ordering Information:

Part NO.	ZM930P06S
Marking	ZM930P06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	-3.5	A
	$I_{D@TC=75^\circ C}$	-2.7	A
	$I_{D@TC=100^\circ C}$	-2.2	A
Pulsed Drain Current ^①	I_{DM}	-10.5	A
Total Power Dissipation	$P_D@TC=25^\circ C$	50	W
Total Power Dissipation	$P_D@TA=25^\circ C$	1.25	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	37	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.4	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	100	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\mu A$	-1.2		-2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -12A$		93	120	m Ω
		$V_{GS} = -4.5V, I_D = -10A$		128	166	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = -10V, I_D = -2A$		10		S
Source-drain voltage	V_{SD}	$I_S = -12A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{DS} = -25V$ $f = 1MHz$	-	650	-	pF
Output capacitance	C_{oss}		-	120	-	
Reverse transfer capacitance	C_{rss}		-	70	-	

•Gate Charge characteristics($T_a = 25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = -15V$	-	12	-	nC
Gate - Source charge	Q_{gs}	$I_D = -12A$	-	4	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = -10V$	-	6	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Gate-Charge Characteristics

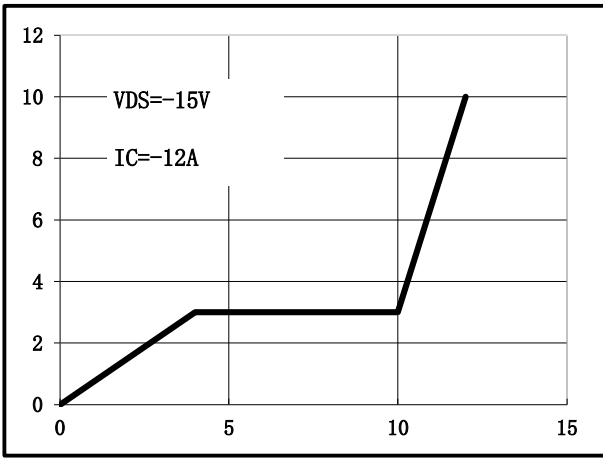


Fig.2 Capacitance Characteristics

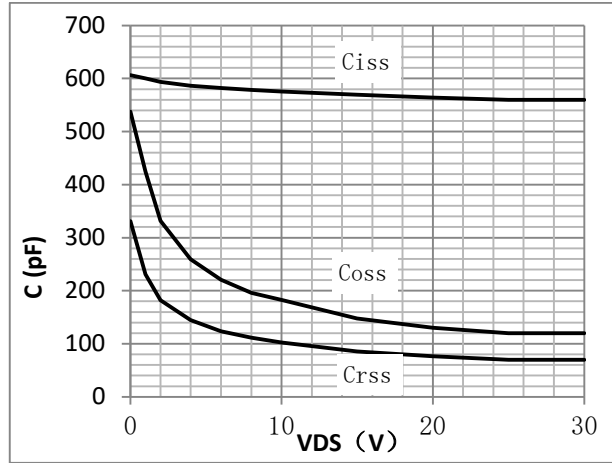


Fig.3 Power Dissipation Derating Curve

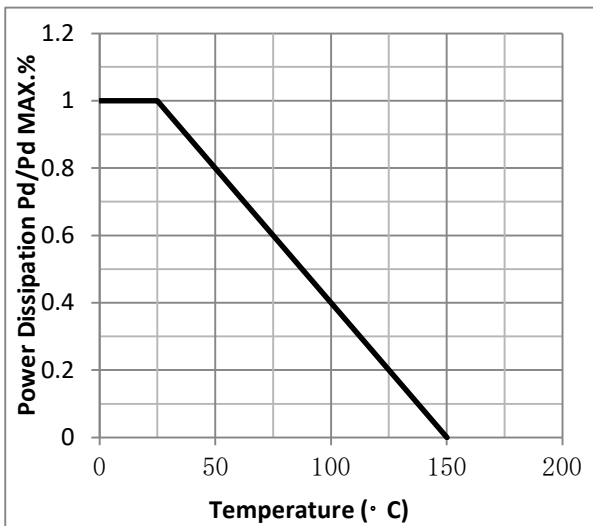


Fig.4 Typical output Characteristics

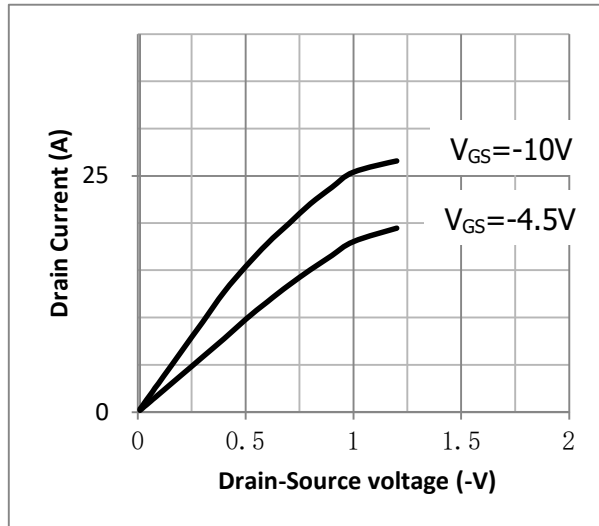


Fig.5 Threshold Voltage V.S Junction Temperature

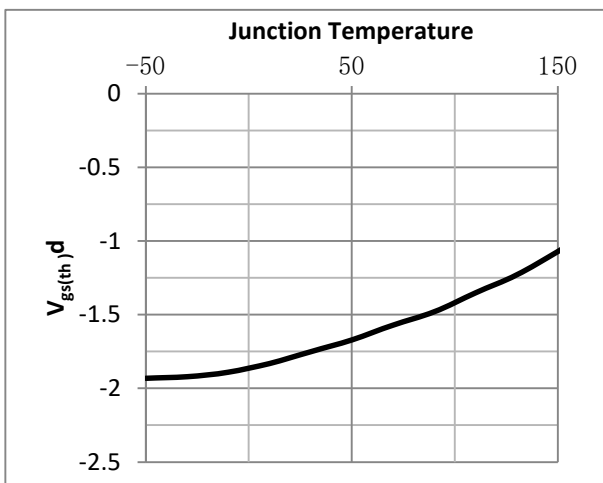


Fig.6 Resistance V.S Drain Current

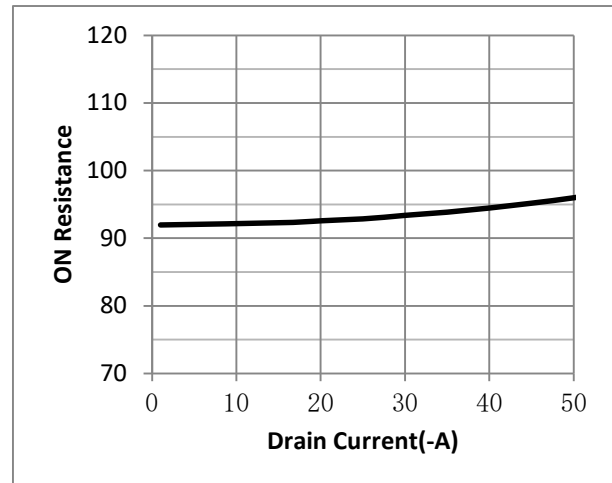


Fig.7 On-Resistance VS Gate Source Voltage

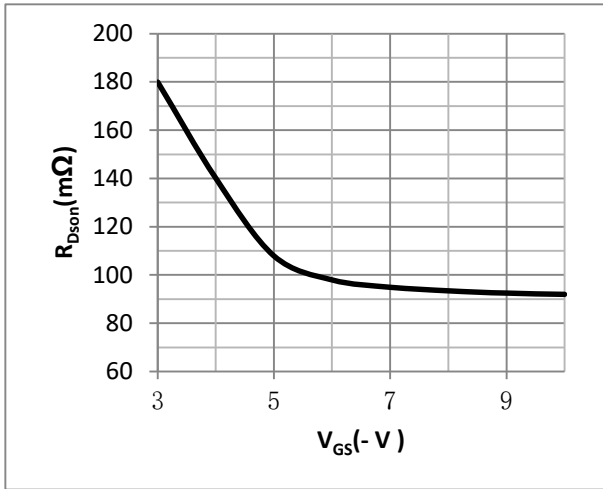


Fig.8 On-Resistance V.S Junction Temperature

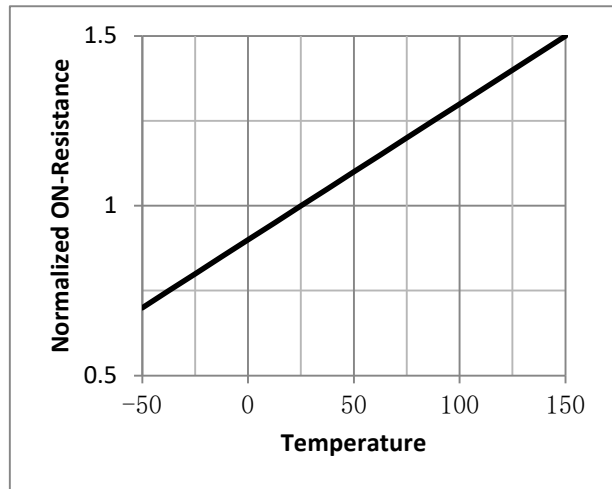


Fig.9 SOA Maximum Safe Operating Area

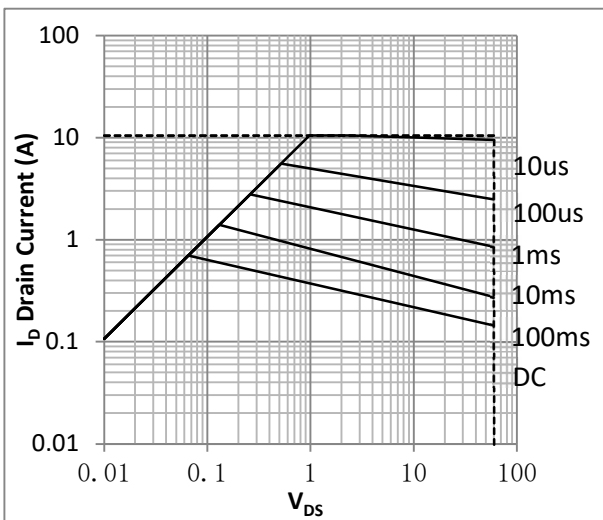


Fig.10 I_D -Junction Temperature

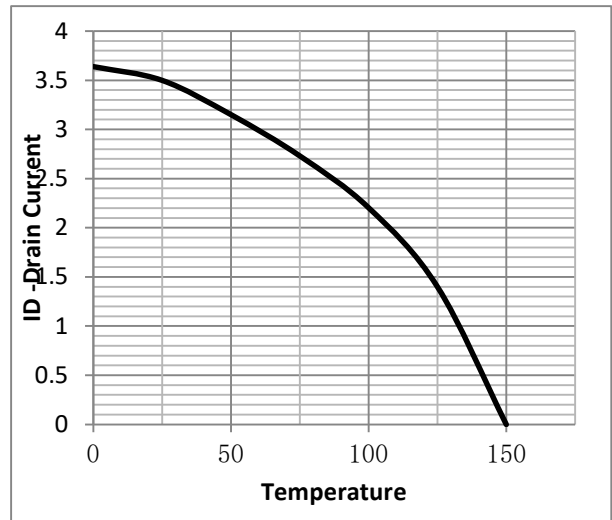


Fig.11 Gate Charge Measurement Circuit

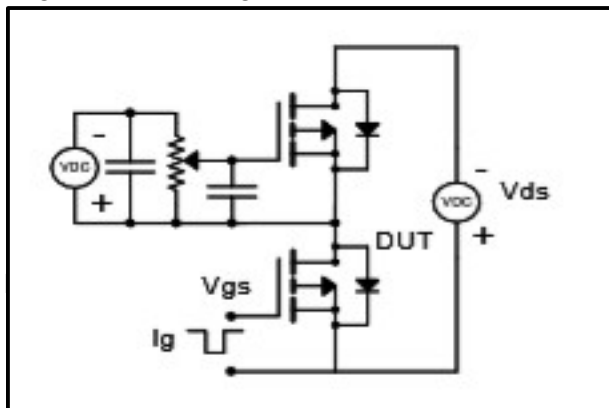


Fig.12 Gate Charge Waveform

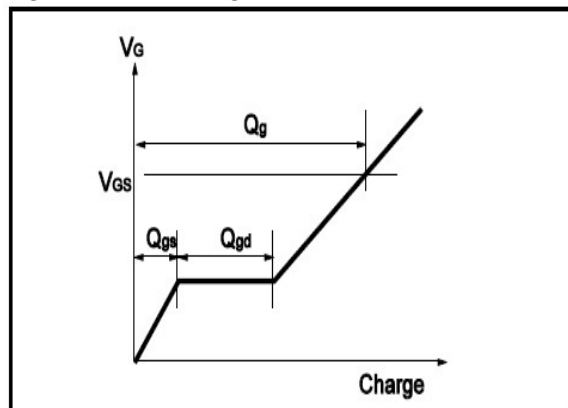


Fig.13 Switching Time Measurement Circuit

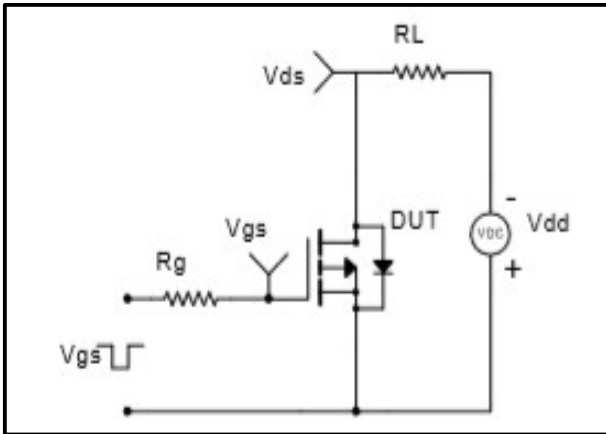


Fig.14 Switching Time Waveform

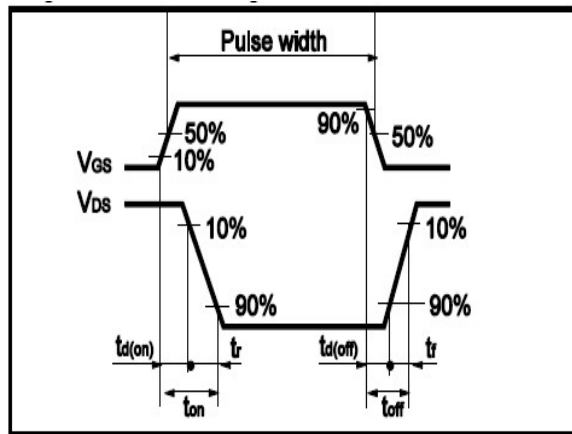


Fig.15 Avalanche Measurement Circuit

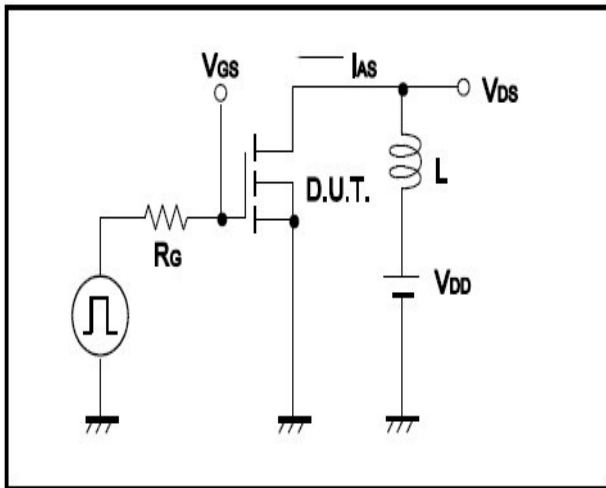
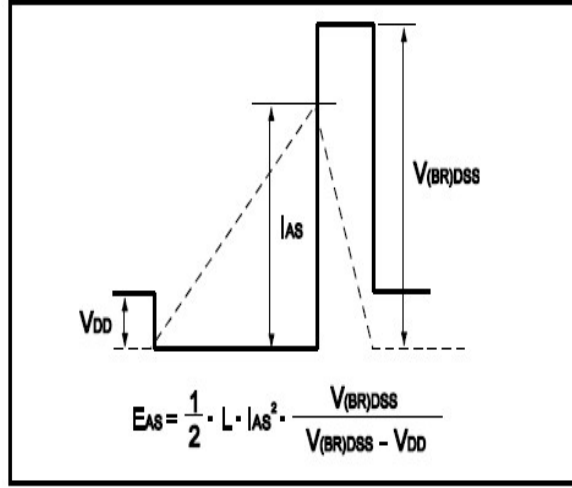


Fig.16 Avalanche Waveform





●Dimensions(SOP-8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.10	D		1.05	
B2		5.00		D1	0.40		0.62

